

SPECIFICATION OF LED CHIP

C610-30V

[ORANGE]

1) Commodity Type and Physical Characteristics.

1. Material	InGaAlP/GaAs	
2. Electrode	Top Side P (anode) side	: Au Alloy/Al Pad
	Bottom Side N (cathode) side	: Au Alloy
3. Electrode Pattern		Fig.1
4. Chip Size		Fig.2
5. Chip Thickness		Fig.2
6. Emission Area		Fig.2

2) Electro-Optical Characteristics

parameters	symbol	condition	min.	typ.	max.	unit
Forward Voltage	V _f	I _f =20mA		2.0	2.4	V
Reverse Current	I _r	V _r =5V			10	uA
Brightness	I _v	I _f =20mA	50	90		mcd
Power Intensity	P _o	I _f =20mA	0.6	1.2		mW
Peak Wavelength	λ _P	I _f =20mA	600	610	620	nm
Spectral Radiation Bandwidth	Δλ	I _f =20mA		20		nm
Rise Time	t _r	I _f =20mA		100		ns
Fulltime	t _f	I _f =20mA		100		ns

‡ Die shall be mounted on TO=18 gold header without resin coated. (T_a=25°C)

[Unit: um]

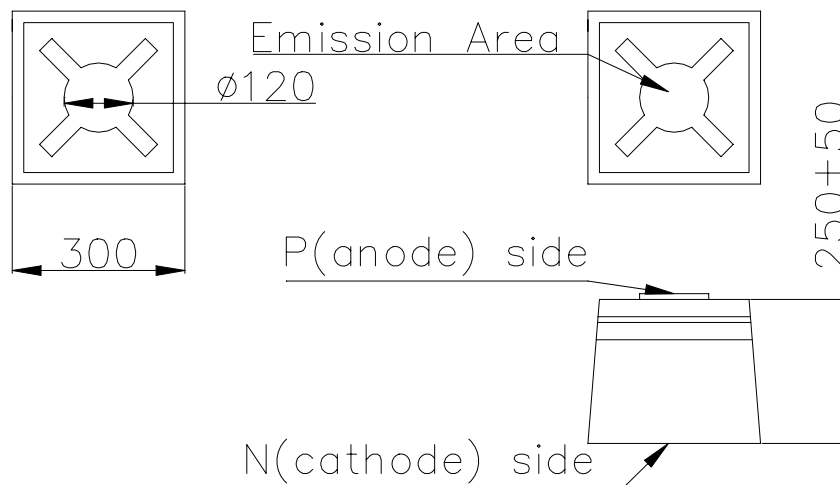


Fig.1 Electrode Pattern

Fig.2 Chip size and Emission Area